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INFORMATION DISCLOSURE CITATION
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(Use several sheets if necessary)

Applicant

Y. Tsuda, et al.

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U.S. PATENT DOCUMENTS

Examiner Initials	Ref. No.	Date	Document No.	Name	Class	Subclass	Filing Date If Appropriate

FOREIGN PATENT DOCUMENTS

Examiner Initials	Ref. No.	Date	Document No.	Country	Class	Subclass	Translation YES NO

OTHER DOCUMENTS

(including author, title, Date, Pertinent Pages, Etc.)

Examiner Initials	Ref. No.	Title
Duplicate	1.	Sunakawa et al. (1997). "Thick GaN crystal growth with low defect density by hydride vapor phase epitaxy" Ext. Abstract. (The 58th Autumn Meeting) J. Soc. of Appl. Phys. No. 1-266 2p-Q-15
	2.	Tanaka et al. (1997). "Reduced dislocation densities in selectivity-grown nitride materials" Ext. Abstract. (The 58th Autumn Meeting) J. Soc. of Appl. Phys. No. 1-265 2p-Q-14.

Ref # 1 on Form 852 paper # 3

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